

HALF-BRIDGE DRIVER

Features

- Floating channel designed for bootstrap operation Fully operational to +600V Tolerant to negative transient voltage dV/dt immune
- Gate drive supply range from 10 to 20V
- Undervoltage lockout for both channels
- 3.3V, 5V and 15V input logic compatible
- Cross-conduction prevention logic
- Matched propagation delay for both channels
- High side output in phase with IN input
- Logic and power ground +/- 5V offset.
- Internal 540ns dead-time, and programmable up to 5us with one external R_{DT} resistor (IR21094)
- Lower di/dt gate driver for better noise immunity
- Shut down input turns off both channels.
- Available in Lead-Free

Description

The IR2109(4)(S) are high voltage, high speed power MOSFET and IGBT drivers with dependent high and low side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable rugge-dized monolithic construction. The logic input is compatible with standard CMOS or LSTTL output, down to 3.3V logic. The output drivers feature a high

Product Summary

VOFFSET 600V max.

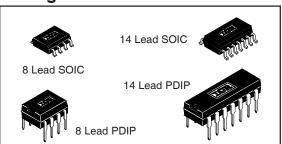
IO+/- 120 mA / 250 mA

VOUT 10 - 20V

ton/off (typ.) 750 & 200 ns

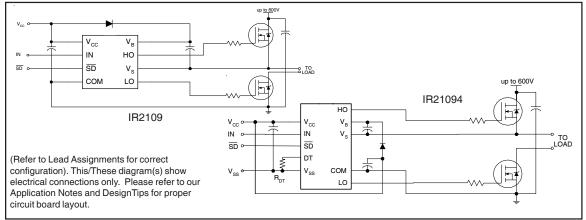
Dead Time 540 ns
(programmable up to 5uS for IR21094)

Packages



pulse current buffer stage designed for minimum driver cross-conduction. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration which operates up to 600 volts.

Typical Connection



Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition		Min.	Max.	Units			
V _B	High side floating absolute voltage	-0.3	625					
Vs	High side floating supply offset voltage	V _B - 25	V _B + 0.3					
V _{HO}	High side floating output voltage	V _S - 0.3	V _B + 0.3					
V _{CC}	Low side and logic fixed supply voltage		-0.3	25	.,			
V _{LO}	Low side output voltage	-0.3	V _{CC} + 0.3	─				
DT	Programmable dead-time pin voltage (IR21	V _{SS} - 0.3	V _{CC} + 0.3					
V _{IN}	Logic input voltage (IN & SD)	V _{SS} - 0.3	V _{CC} + 0.3					
V _{SS}	Logic ground (IR21094/IR21894 only)		V _{CC} - 25	V _{CC} + 0.3	1			
dV _S /dt	Allowable offset supply voltage transient		_	50	V/ns			
PD	Package power dissipation @ T _A ≤ +25°C	(8 Lead PDIP)	_	1.0				
		(8 Lead SOIC)	_	0.625				
		(14 lead PDIP)	_	1.6	W			
		(14 lead SOIC)	_	1.0				
RthJA	Thermal resistance, junction to ambient	(8 Lead PDIP)	_	125				
		(8 Lead SOIC)	_	200	°C/W			
		(14 lead PDIP)	_	75				
		(14 lead SOIC)	_	120	Ī			
TJ	Junction temperature		_	150				
T _S	Storage temperature		-50	150	°C			
TL	Lead temperature (soldering, 10 seconds)		_	300				

Recommended Operating Conditions

The input/output logic timing diagram is shown in figure 1. For proper operation the device should be used within the recommended conditions. The V_S and V_{SS} offset rating are tested with all supplies biased at 15V differential.

Symbol	Definition	Min.	Max.	Units
VB	High side floating supply absolute voltage	V _S + 10	V _S + 20	
Vs	High side floating supply offset voltage	Note 1	600	
V _{HO}	High side floating output voltage	Vs	V _B	
Vcc	Low side and logic fixed supply voltage	10	20	
V _{LO}	Low side output voltage	0	V _{CC}	V
V _{IN}	Logic input voltage (IN & SD)	V _{SS}	V _{CC}	
DT	Programmable dead-time pin voltage (IR21094 only)	V _{SS}	V _{CC}	
Vss	Logic ground (IR21094 only)	-5	5	
T _A	Ambient temperature	-40	125	°C

Note 1: Logic operational for V_S of -5 to +600V. Logic state held for V_S of -5V to -V_{BS}. (Please refer to the Design Tip DT97-3 for more details).

Dynamic Electrical Characteristics

 V_{BIAS} (V_{CC}, V_{BS}) = 15V, V_{SS} = COM, C_L = 1000 pF, T_A = 25°C, DT = VSS unless otherwise specified.

Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
ton	Turn-on propagation delay	_	750	950		V _S = 0V
toff	Turn-off propagation delay	_	200	280		V _S = 0V or 600V
tsd	Shut-down propagation delay	_	200	280		
MT	Delay matching, HS & LS turn-on/off	_	0	70	nsec	
t _r	Turn-on rise time	_	150	220		V _S = 0V
tf	Turn-off fall time	_	50	80		V _S = 0V
DT	Deadtime: LO turn-off to HO turn-on(DTLO-HO) &	400	540	680		RDT= 0
	HO turn-off to LO turn-on (DTHO-LO)	4	5	6	usec	RDT = 200k (IR21094)
MDT	Deadtime matching = DTLO - HO - DTHO-LO	_	0	60	nsec	RDT=0
		_	0	600	1.300	RDT = 200k (IR21094)

International

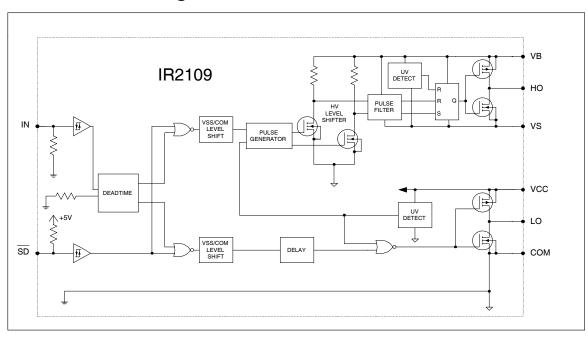
TOR Rectifier

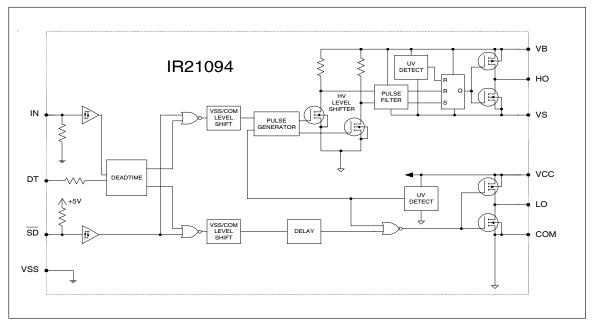
Static Electrical Characteristics

 V_{BIAS} (V_{CC} , V_{BS}) = 15V, V_{SS} = COM, DT= V_{SS} and T_A = 25°C unless otherwise specified. The $\overline{V_{IL}}$, V_{IH} and I_{IN} parameters are referenced to V_{SS} /COM and are applicable to the respective input leads: IN and \overline{SD} . The V_O , I_O and Ron parameters are referenced to COM and are applicable to the respective output leads: HO and LO.

Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
V _{IH}	Logic "1" input voltage for HO & logic "0" for LO	2.9	_	_		V _{CC} = 10V to 20V
V _{IL}	Logic "0" input voltage for HO & logic "1" for LO	_	_	0.8		V _{CC} = 10V to 20V
V _{SD,TH+}	SD input positive going threshold	2.9	_	_	.,	V _{CC} = 10V to 20V
V _{SD,TH} -	SD input negative going threshold	_	_	0.8	V	V _{CC} = 10V to 20V
V _{OH}	High level output voltage, V _{BIAS} - V _O	_	0.8	1.4		I _O = 20 mA
V _{OL}	Low level output voltage, VO	_	0.3	0.6		I _O = 20 mA
I _{LK}	Offset supply leakage current	_	_	50		$V_{B} = V_{S} = 600V$
I _{QBS}	Quiescent V _{BS} supply current	20	75	130	μA	V _{IN} = 0V or 5V
IQCC	Quiescent V _{CC} supply current	0.4	1.0	1.6	mA	V _{IN} = 0V or 5V
						RDT = 0
I _{IN+}	Logic "1" input bias current	_	5	20	_	$IN = 5V, \overline{SD} = 0V$
I _{IN} -	Logic "0" input bias current	_	_	2	μA	IN = 0V, SD = 5V
V _{CCUV+}	$V_{\mbox{\footnotesize{CC}}}$ and $V_{\mbox{\footnotesize{BS}}}$ supply undervoltage positive going	8.0	8.9	9.8		
V _{BSUV+}	threshold					
V _{CCUV} -	V _{CC} and V _{BS} supply undervoltage negative going	7.4	8.2	9.0		
V _{BSUV} -	threshold				V	
VCCUVH	Hysteresis	0.3	0.7	_		
V _{BSUVH}						
I _{O+}	Output high short circuit pulsed vurrent	120	200	_	A	$V_O = 0V$, $PW \le 10 \mu s$
I _{O-}	Output low short circuit pulsed current	250	350	_	mA	$V_O = 15V,PW \le 10 \mu s$

Functional Block Diagrams





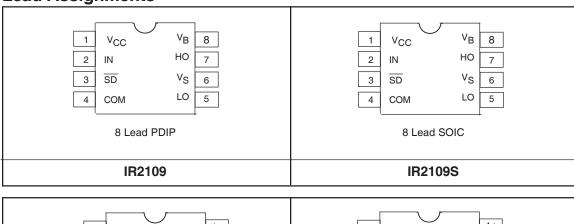
International

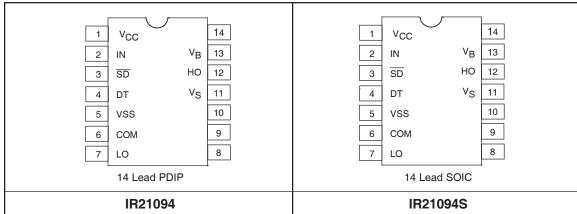
TOR Rectifier

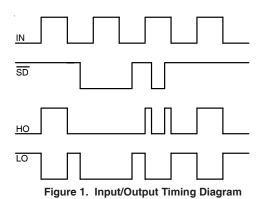
Lead Definitions

Symbol	Description
IN	Logic input for high and low side gate driver outputs (HO and LO), in phase with HO (referenced to COM
	for IR2109 and VSS for IR21094)
SD	Logic input for shutdown (referenced to COM for IR2109 and VSS for IR21094)
DT	Programmable dead-time lead, referenced to VSS. (IR21094 only)
VSS	Logic Ground (21094 only)
V _B	High side floating supply
НО	High side gate drive output
Vs	High side floating supply return
V _{CC}	Low side and logic fixed supply
LO	Low side gate drive output
СОМ	Low side return

Lead Assignments







IN(LO)

50%

50%

ton

ton

ton

toff

4

90%

90%

10%

Figure 2. Switching Time Waveform Definitions

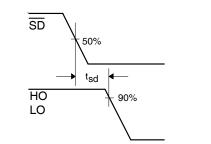


Figure 3. Shutdown Waveform Definitions

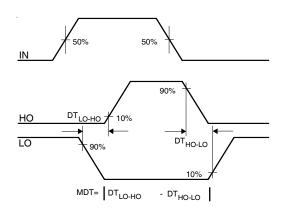


Figure 4. Deadtime Waveform Definitions

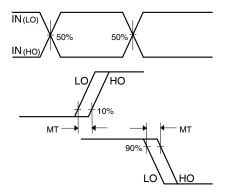


Figure 5. Delay Matching Waveform Definitions

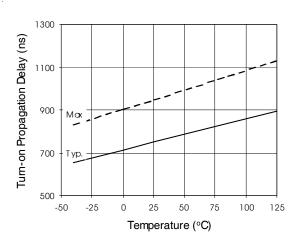


Figure 6A. Turn-on Propagation Delay vs. Temperature

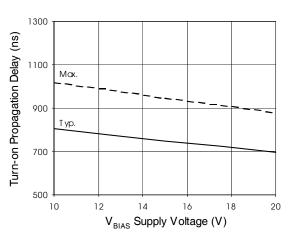


Figure 6B. Turn-on Propagation Delay vs. Supply Voltage

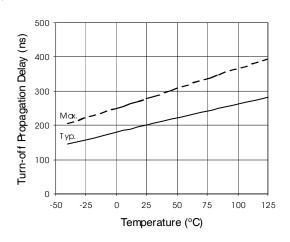


Figure 7A. Turn-off Propagation Delay vs. Temperature

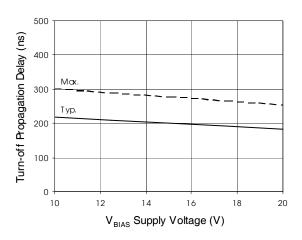


Figure 7B. Turn-off Propagation Delay vs. Supply Voltage

International TOR Rectifier

IR2109(4) (s) & (PbF)

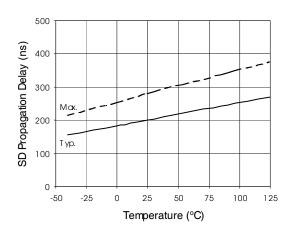


Figure 8A. SD Propagation Delay vs. Temperature

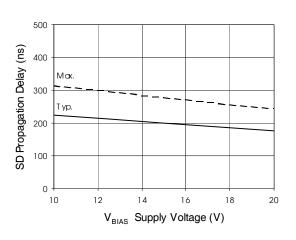


Figure 8B. SD Propagation Delay vs. Supply Voltage

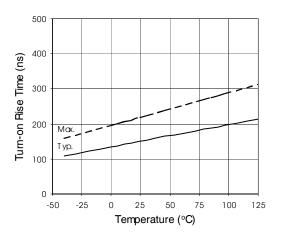


Figure 9A. Turn-on Rise Time vs. Temperature

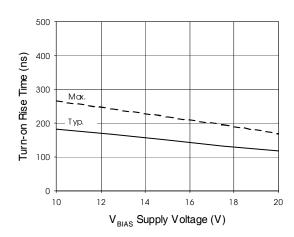


Figure 9B. Turn-on Rise Time vs. Supply Voltage

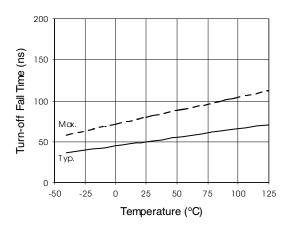


Figure 10A. Turn-off Fall Time vs. Temperature

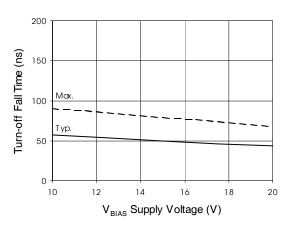


Figure 10B. Turn-off Fall Time vs. Supply Voltage

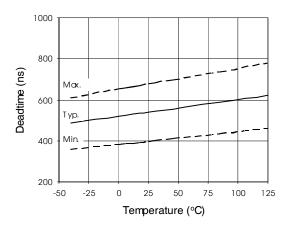


Figure 11A. Deadtime vs. Temperature

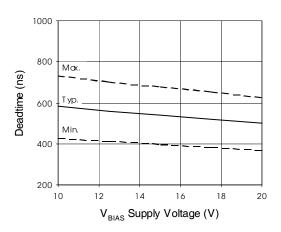


Figure 11B. Deadtime vs. Supply Voltage

International Rectifier

IR2109(4) (s) & (PbF)

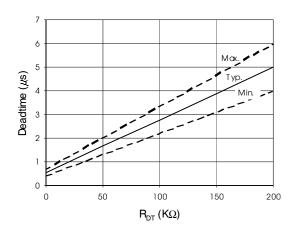


Figure 11C. Deadtime vs. R_{DT} (IR21094 only)

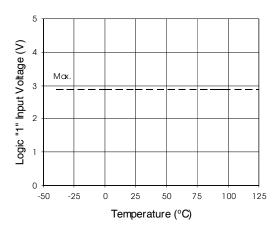


Figure 12A. Logic "1" Input Voltage vs. Temperature

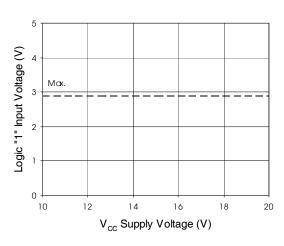


Figure 12B. Logic "1" Input Voltage vs. Supply Voltage

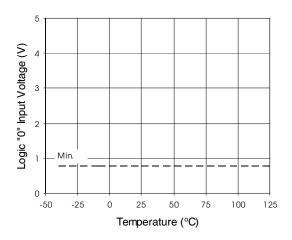


Figure 13A. Logic "0" Input Voltage vs. Temperature

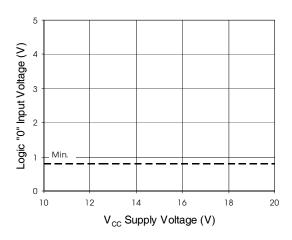


Figure 13B. Logic "0" Input Current vs. Supply Voltage

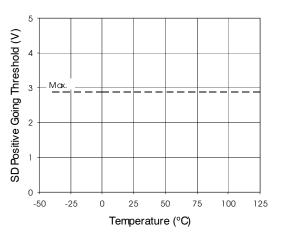


Figure 14A. SD Positive Going Threshold vs. Temperature

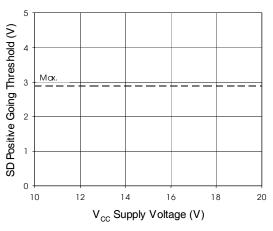


Figure 14B. SD Positive Going Threshold vs. Supply Voltage

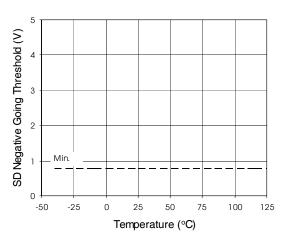


Figure 15A. SD Negative Going Threshold vs. Temperature

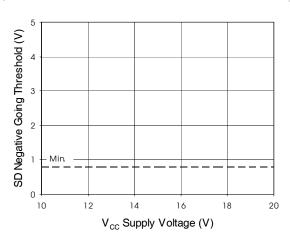


Figure 15B. SD Negative Going Threshold vs. Supply Voltage

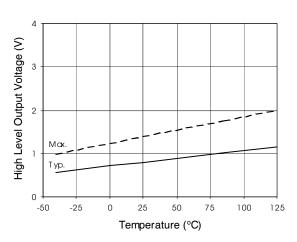


Figure 16A. High Level Output Voltage vs. Temperature

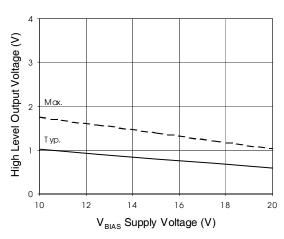


Figure 16B. High Level Output Voltage vs. Supply Voltage

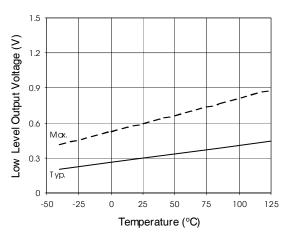


Figure 17A. Low Level Output Voltage vs. Temperature

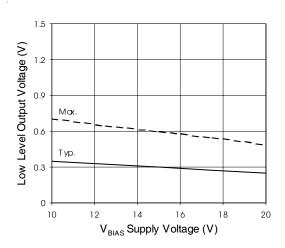


Figure 17B. Low Level Output Voltage vs. Supply Voltage

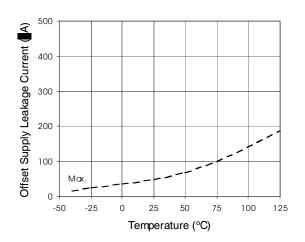
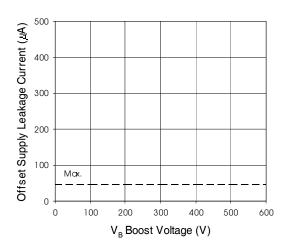


Figure 18A. Offset Supply Leakage Current vs. Temperature



igure 18B. Offset Supply Leakage Current vs. Boost Voltage

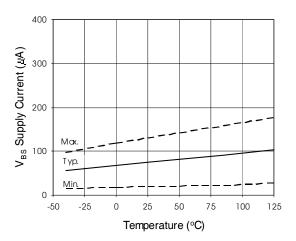


Figure 19A. VBS Supply Current vs. Temperature

International TOR Rectifier

IR2109(4) (s) & (PbF)

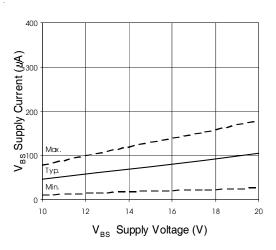
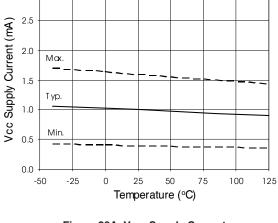


Figure 19B. VBS Supply Current vs. Supply Voltage



3.0

Figure 20A. V_{CC} Supply Current vs. Temperature

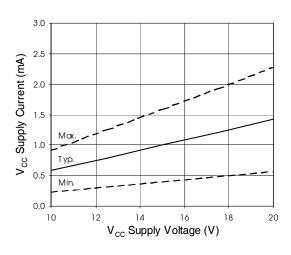


Figure 20B. V_{CC} Supply Current vs. V_{CC} Supply Voltage

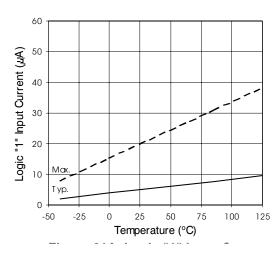


Figure 21A. Logic "1" Input Current vs. Temperature

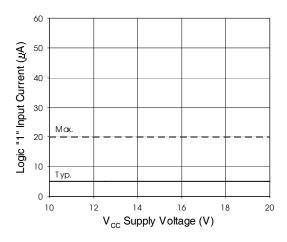


Figure 21B. Logic "1" Input Current vs. Supply Voltage

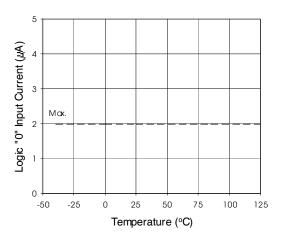


Figure 22A. Logic "0" Input Current vs. Temperature

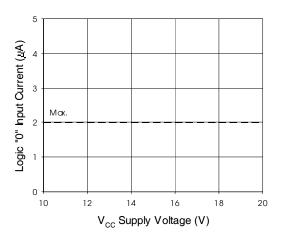


Figure 22B. Logic "0" Input Currentt vs. Supply Voltage

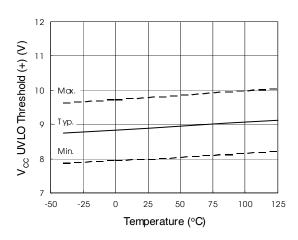


Figure 23. VCC Undervoltage Threshold (+) vs. Temperature

International TOR Rectifier

IR2109(4) (s) & (PbF)

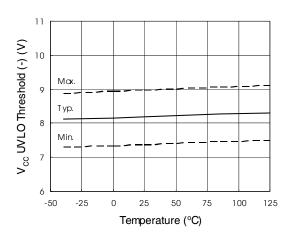


Figure 24. VCC Undervoltage Threshold (-) vs. Temperature

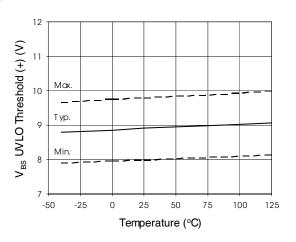


Figure 25. VBS Undervoltage Threshold (+) vs. Temperature

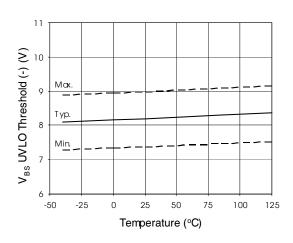


Figure 26. VBS Undervoltage Threshold (-) vs. Temperature

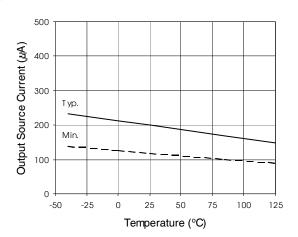


Figure 27A. Output Source Current vs. Temperature

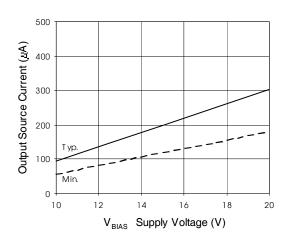


Figure 27B. Output Source Current vs. Supply Voltage

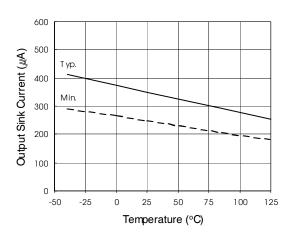


Figure 28A. Output Sink Current vs. Temperature

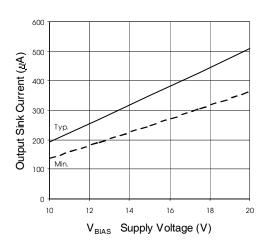


Figure 28B. Output Sink Currentt vs. Supply Voltage

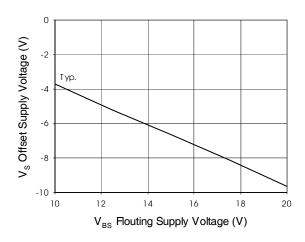
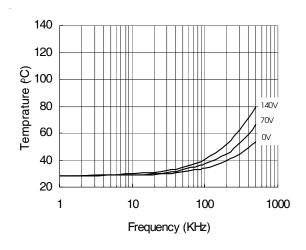


Figure 29. Maximum VS Negative Offset vs. Supply Voltage

International Rectifier

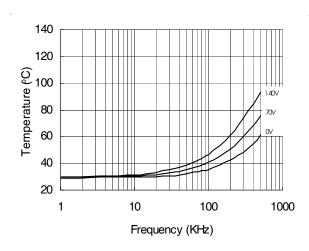
IR2109(4) (s) & (PbF)



140 120 100 80 60 40 20 1 10 100 1000 Frequency (KHz)

Figure 30. IR2109 vs Frequency (IRFBC20) $R_{\mbox{\scriptsize qate}} = 33\Omega, \ \mbox{\scriptsize VCC} = 15\mbox{\scriptsize V}$

Figure 31. IR2109 vs Frequency (IRFBC30) $R_{\mbox{gate}} = 22\Omega, \ \mbox{VCC} = 15 \mbox{V}$



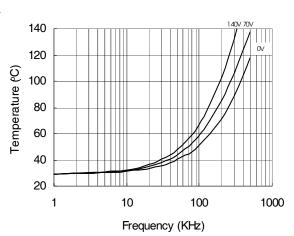


Figure 32. IR2109 vs Frequency (IRFBC40) $R_{\mbox{gate}} = 15\Omega, \ \mbox{VCC} = 15\mbox{V}$

Figure 33. IR2109 vs Frequency (IRFPE50) $R_{\mbox{\scriptsize qate}} = 10\Omega, \ \mbox{\scriptsize VCC} = 15\mbox{\scriptsize V}$

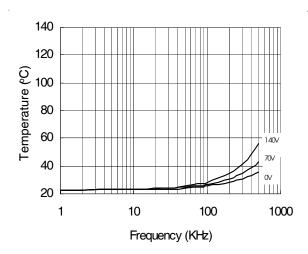


Figure 34. IR21094 vs. Frequency (IRFBC20), ${\rm R_{\rm qate}}{=}33\Omega,\,{\rm V_{\rm CC}}{=}15{\rm V}$

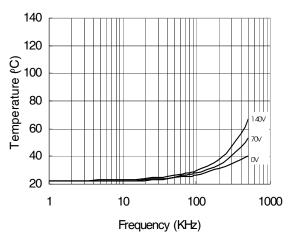


Figure 35. IR21094 vs. Frequency (IRFBC30), ${\rm R_{gate}}{=}22\Omega,\,{\rm V_{CC}}{=}15{\rm V}$

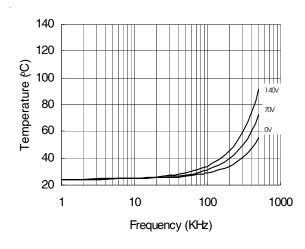


Figure 36. IR21094 vs. Frequency (IRFBC40), ${\rm R_{\rm qate}}{=}15\Omega, {\rm V_{\rm CC}}{=}15{\rm V}$

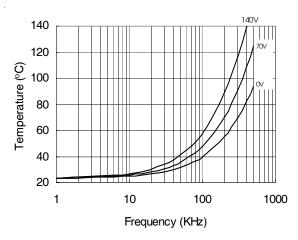


Figure 37. IR21094 vs. Frequency (IRFPE50), ${\rm R_{\rm nate}}{=}10\Omega,\,{\rm V_{\rm CC}}{=}15{\rm V}$

International Rectifier

IR2109(4) (s) & (PbF)

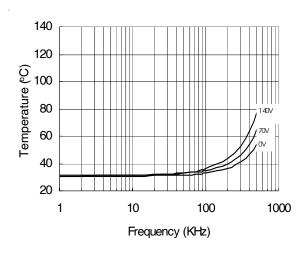


Figure 38. IR2109S vs. Frequency (IRFBC20), ${\rm R_{\rm qate}} {=} 33\Omega, \, {\rm V_{CC}} {=} 15 {\rm V}$

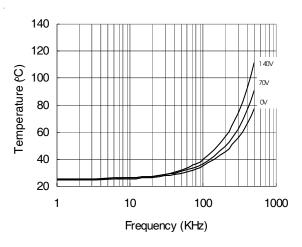


Figure 39. IR2109S vs. Frequency (IRFBC30), ${\rm R_{\rm gate}}{=}22\Omega,\,{\rm V_{\rm CC}}{=}15{\rm V}$

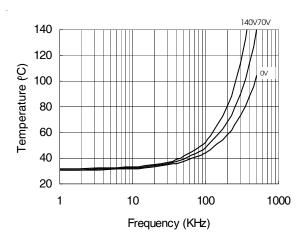


Figure 40. IR2109S vs. Frequency (IRFBC40), ${\rm R_{\rm gate}}{=}15\Omega,\,{\rm V_{\rm CC}}{=}15{\rm V}$

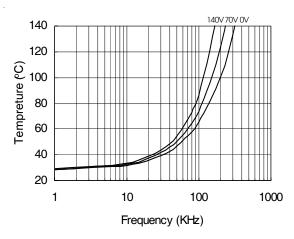


Figure 41. IR2109S vs. Frequency (IRFPE50), R_{oate} =10 Ω , V_{cc} =15V

International TOR Rectifier

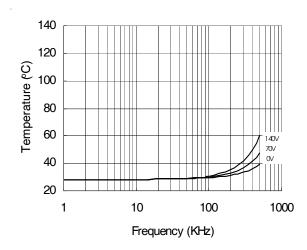


Figure 42. IR21094S vs. Frequency (IRFBC20), ${\rm R_{gate}}{=}33\Omega,\,{\rm V_{CC}}{=}15{\rm V}$

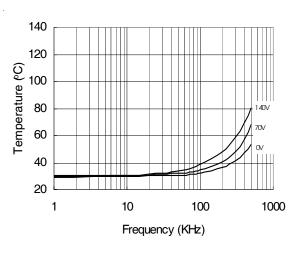


Figure 43. IR21094S vs. Frequency (IRFBC30), ${\rm R_{\rm qate}}{=}22\Omega,\,{\rm V_{\rm CC}}{=}15{\rm V}$

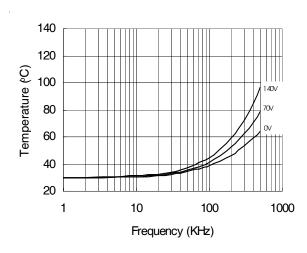


Figure 44. IR21094S vs. Frequency (IRFBC40), ${\rm R_{\rm oate}}{=}15\Omega,\,{\rm V_{\rm cc}}{=}15{\rm V}$

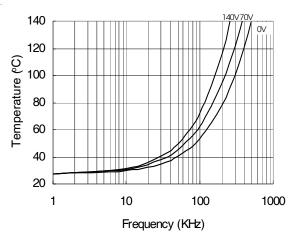
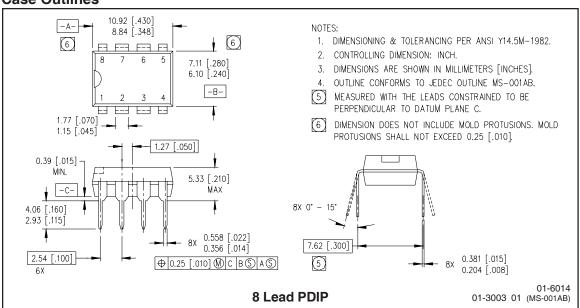
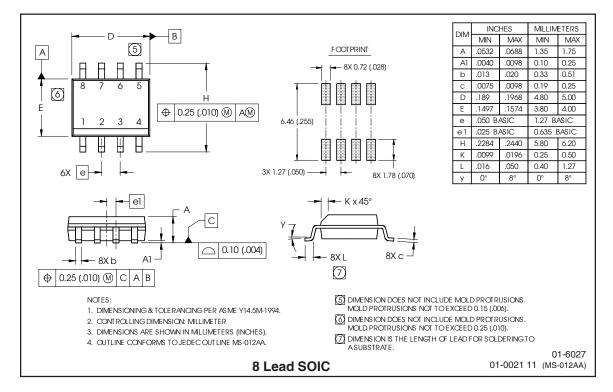
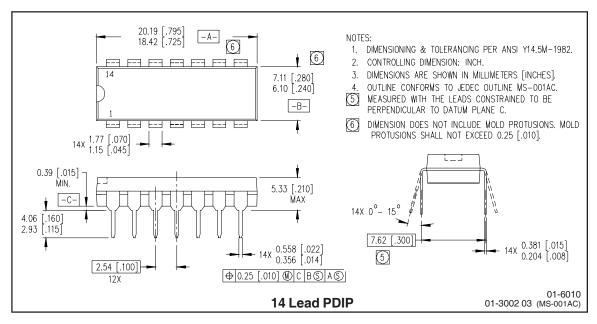


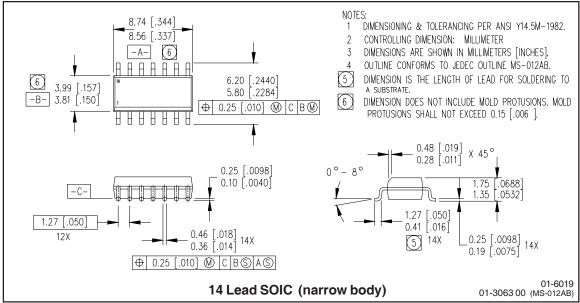
Figure 45. IR21094S vs. Frequency (IRFPE50), ${\rm R_{\rm qate}}{=}10\Omega,\,{\rm V_{\rm CC}}{=}15{\rm V}$

Case Outlines



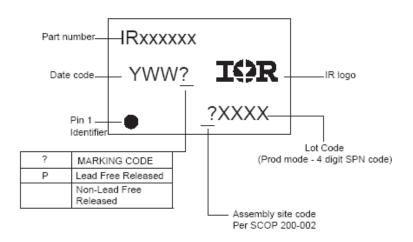






Data and specifications subject to change without notice. 7/11/2003

LEADFREE PART MARKING INFORMATION



Basic Part (Non-Lead Free)

Lead-Free Part

8-Lead PDIP IR2	2109	order	IR2109
8-Lead SOIC IR2	2109S	order	IR2109S
14-Lead PDIP IR2	21094	order	IR21094
14-Lead SOIC IR2	21094S	order	IR21094S

8-Lead PDIP IR2109 order IR2109PbF 8-Lead SOIC IR2109S order IR2109SPbF 14-Lead PDIP IR21094 order IR21094PbF 14-Lead SOIC IR21094S order IR21094SPbF



This product has been designed and qualified for the Industrial market.

Qualification Standards can be found on IR's Website.

Data and specifications subject to change without notice.

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